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# Index

- $k_1$  factor, 28
  - trend, 29
- 1-Gb DRAM critical levels, 153
- aberration
  - alternating phase-shifting mask, 126
  - effect on side-lobe, 145
  - off-axis illumination, 88
- aberration sensitivity, 126, 173
- alternating phase-shifting mask
  - aberration sensitivity, 126
  - additive process, 122
  - comparison with attenuated phase-shifting mask, 141
  - computer-aided design, 133
  - cost, 138
  - dark-field application, 131–133
    - design rules, 131
    - pattern density increase, 131
  - defects, 128
  - differential imaging, 129
  - effective errors, 126
  - effective transmission and phase, 126
  - enhanced, 173
  - in conjunction with off-axis illumination, 121
  - intensity imbalance, 123
  - light-field application, 133–137
    - conjugate twin shifter, 135
    - gate-only phase-shifting, 137
    - multiple phase steps, 135
    - pattern density decrease, 135
    - residual phase edge, 133
    - trim mask, *see* trim mask, alternating phase-shifting
  - line placement error, 123
  - phase conflict, 132
  - phase error, 124
  - repair, 130
  - restoring balance, 125
  - side wall scattering, 124
  - space width difference, 123
  - spectrum, 118
  - subtractive process, 121
  - transmission error, 124
- annular illumination, 85–87
  - $\sigma_{\text{inner}}$ , 87
  - $\sigma_{\text{outer}}$ , 87
- antireflective coating, 19
- assist feature, 97
  - phase-shifting, 131, 140
- asymmetric subgrid biasing, 96
- attenuated phase-shifting mask
  - alignment problem, 149
  - carbon thin-film, 148
  - comparison with alternating phase-shifting mask, 141
  - comparison with chromium-on-glass mask, 143
  - cost, 151
  - fabrication process, 150
  - first generation, 147
  - in conjunction with off-axis illumination, 143
  - inspection problem, 149
  - issues, 151
  - opaque border, 148–150

- spectrum, 141
- thin-film materials, 148
- transmission level, 147
- undesired multiple exposure, 148
- BIM, *see* binary-intensity mask
- binary-intensity mask, 12
- borderless contact, 168
- borosilicate glass, 11
- Bossung plot, 65
- chromium-on-glass mask, 11, 12
  - comparison with attenuated phase-shifting mask, 143
- COG, *see* chromium-on-glass mask
- compensating process, 180
- complex degree of coherence, 55
  - annular illumination, 86
  - dipole illumination, 83
  - partially coherent imaging, 57
  - quadrupole illumination, 84
- computer-aided design, 4, 183
  - alternating phase-shifting mask, 133
  - optical proximity correction, 110
- concurrent reticle-illumination optimization, 176
- contact hole
  - alternating phase-shifting mask application, 131
  - attenuated phase-shifting mask benefit, 139
  - bit line, 166
  - pupil filtering, 176
  - rectangular, 168
  - resolution limit, 64
- contact printing, 14
- contrast
  - image, *see* image quality quantification, contrast
- contrast enhancement layer, 20
- corner rounding, 92, 100
- correct-negative design, 10
- correct-positive design, 10
- cost of ownership, 24
- cross-disciplinary optimization, 184
- dark-field illumination, 177
- delta function, *see* Dirac delta function
- dense pattern, 78
- depth of focus, *see* image quality quantification, depth of focus
  - enhancement by multiple exposure, 175
- design grid, 95
- diffracted order, *see* mask spectrum
  - zero magnitude, 43, 120
- dipole illumination, 80–83
  - asymmetry, 83
- Dirac delta function, 35
- direct write lithography, 26, 185
- dose-to-clear, 22
- dose-to-gel, 22
- effective mask size, 11
- effective source, 47–48
- effective threshold, 181
- effective transmission and phase, *see* alternating phase-shifting mask, effective transmission and phase
- electron beam projection lithography, 26
- embedded phase-shifting mask, 148
- enhanced alternating phase-shifting mask, 173
- EUV lithography, *see* extreme ultraviolet lithography
- excimer laser, 6
- exposure latitude, *see* image quality quantification, exposure latitude
- exposure system, 13–18
- extreme ultraviolet lithography, 26

- FLEX, 175
- forbidden pitch, 100, 183
- fused silica, 12
- g-line, 6
- Gibbs phenomenon, 145
- halftone biasing, 95
- halftone mask, 148
- hammer head, 100
- history
  - lithography, 1
  - optical lithography, 13
  - printing, 1
- Huygen's principle, 17
- i-line, 6
- IDEAL, 172
- image contrast, *see* image quality quantification, contrast
- image quality quantification, 59–70
  - common window, 68
  - contrast, 60
  - depth of focus, 62
  - exposure latitude, 60
  - exposure-defocus window, 64
  - linewidth variation, 69
  - log slope, 61
  - modulation transfer function, *see* modulation transfer function
  - need of metric, 183
  - normalized image log slope, 61
  - total window, 66
- imprint lithography, 26
- impulse response, *see* point spread function
- integrated circuit
  - creation, 2–4
  - design, 4
  - fabrication, 4
- ion projection lithography, 26
- Köhler's illumination method, 7
- large  $\sigma$ , 71–79
  - relative advantage, *see* off-axis point source, relative advantage
- Levenson phase-shifting mask, *see* alternating phase-shifting mask
- line
  - definition, 9
- line edge roughness, 27
- line lengthening, 100
- line shortening, 92, 100
  - reduction by multiple exposure, 173
- lithography-friendly design, 28, 184
- log slope, *see* image quality quantification, normalized image log slope
- mask bias
  - definition, 11
  - process window, 68, 157
- mask constraint, 114, 115
  - correction goal, 108
  - grid size, 95
  - model-based OPC, 105
  - serif, 101
  - verification, 115
- mask error enhancement factor, *see* mask error factor
- mask error factor, 11
  - alternating phase-shifting mask, 121
  - contact hole, 180
  - effects on CD control, 165
  - ramification on biasing, 166
- mask inspection
  - challenge, 183
- mask spectrum, 39
  - alternating phase-shifting mask, 118

- attenuated phase-shifting mask, 141
- chromium-on-glass mask, 37
- dependence on dimension, 42
- pitch dependence, 42
- two-dimensional patterns, 44
- mask tone, 10, 180
- mask topography, 126
- Maxwell's equations, 126
- medium  $\sigma$ , 79
- MEF, *see* mask error factor
- mercury arc lamp, 6
- microlithography
  - nonphotolithography techniques, 26
  - optical lithography, *see* optical lithography
  - requirements, 24
- modulation transfer function, 50, 60
- Moore's law, 171
- MTF, *see* modulation transfer function
- multiple exposure, 171–175
- nonlinearity, 91
- nontelecentricity, 75, 79
  - effective, 88
- normalized log slope, *see* image quality quantification, normalized image log slope
- numerical aperture, 24, 29, 31
- off-axis illumination
  - aberration sensitivity, 88
  - issues, 87
- off-axis point source, 73
  - image shift with focus, 75
  - loss of exposure latitude, 74
  - nontelecentricity, *see* nontelecentricity
  - relative advantage, 76
- on-axis point source, 73
- optical imaging
  - coherent, 31–39
  - incoherent, 53
  - partially coherent, 45–53
- optical interaction range
  - annular illumination, 87
  - dipole illumination, 83
  - partially coherent imaging, 58
  - ramification on optical proximity correction, 102
- optical lithography
  - $k_1$  factor, *see*  $k_1$  factor
  - challenges, 27
  - contribution to circuit miniaturization, 6
  - current capabilities, 26
  - general description, 2
  - history, 13
  - light source, 6–8
  - mask, *see* mask-related subjects, 8–13
  - requirements, 24
  - resolution
    - three parameters affecting, 28
  - wavelengths, 28
- optical proximity correction
  - catastrophic, 93
  - comparison of numerical techniques, 105
  - computer-aided design, 110
  - constraint, *see* mask constraint
  - correctable error sources, 106
  - correction function, 108
  - correction goals, 108
  - design rule checker, 102
  - designer's intent, 115
  - error characterization, 107
    - data gathering and analysis, 108
    - process changes, 108
  - error sources, *see* patterning error, sources
  - fracturing, *see* optical proxim-



- ity correction, segmentation
- hierarchy management, 113
- hybrid, 105–106
- model-based, 103–105
  - backward, 104
  - forward, 104
  - kernel, 103
- rule-based, 102–103
- segmentation, 110
  - edge-centric, 110
  - environment, 110
  - even, 110
  - shape-centric, 110
- semicorrectable error sources, 107
- verification, 113
- optimization methodology, 153
- partial coherence factor, 8, 24, 48
  - large  $\sigma$ , *see* large  $\sigma$
  - maximum, 79
  - medium  $\sigma$ , *see* medium  $\sigma$
  - minimum, 79
  - small  $\sigma$ , *see* small  $\sigma$
- pattern correction, 92
- patterning error
  - sources, 106, 171
- pellicle, 9
- phase-shifting
  - alternating, *see* alternating phase-shifting mask
  - attenuated, *see* attenuated phase-shifting mask
  - chromeless, 13
  - dark-field illumination, 179
  - embedded, 148
  - halftone, 148
  - Levenson, *see* alternating phase-shifting mask
  - mask types, 12
  - rim, 12
- photolithography, *see* optical lithography
- photoresist, 18–23
  - acid diffusion length, 157
  - benefit of negative tone, 159
  - contrast, 21, 157
  - development, 23
  - grade, 157
  - negative, 21
  - positive, 21
  - tone, 180
- point spread function, 168, 176
- printing
  - impact on civilization, 1
  - three ingredients, 1
- process window
  - mask bias, *see* mask bias, process window
  - quantification, *see* image quality quantification
- projection printing, 15
- proximity effect, 91
  - dark-field and light-field masks, 164
- proximity printing, 14
- pupil filtering, 175
- quadrupole illumination, 84
  - weak, 84
- raster-scan mask writer, 95
- Rayleigh unit of defocus, 63
- RELACS, 180
- resolution enhancement technique
  - effects on overlay and alignment, 169
  - general applicability, 156
  - guidance based on experience, 169
  - strong, 141, 183
  - use of intuition, 160
  - weak, 141, 183
- resolution limit, 185
  - coherent
    - isolated space, 37

- periodic pattern, 39
  - contact hole, *see* contact hole, resolution limit
  - line, 61
  - nebulous, 59
  - optical lithography, 59
  - partially coherent, 53
  - Rayleigh's, 58
- scanners, 16
- selective line biasing, 94
- serif, 100
- sharp corners, 172
- shot noise, 20
- side lobe
  - intensity, 145
  - reduction, 168
  - suppression, 145
- side-lobe
  - interaction with aberrations, 145
- simulation
  - aerial image, 157
  - electromagnetic propagation, 126
  - photoresist acid diffusion, 157
  - photoresist development, 157
- simultaneous printing of sparse and dense patterns, 79
- sinc function, 36
- small  $\sigma$ , 79
- space
  - definition, 9
- sparse pattern, 78
- standing wave, 19
- step-and-repeat systems, 15
- step-and-scan systems, 16
- steppers, 15
- strong phase-shifting mask, *see* resolution enhancement technique, strong
- strong resolution enhancement technique, *see* resolution enhancement technique, strong
- super-FLEX, 175
- TCC, *see* transmission cross-coefficient
- threshold resist model, 22
- throughput
  - $\sigma > 1$ , 79
  - alternating phase-shifting mask, 135
  - dark-field illumination, 179
  - line narrowing, 28
  - multiple exposure, 172
  - off-axis illumination, 89
- traditional lithography, 30, 154
- transmission cross-coefficient, 49
- trend
  - $k_1$  factor, *see*  $k_1$  factor, trend process latitude, 172
- trim mask
  - alternating phase-shifting, 134
  - sparse pattern, 173
- two-beam imaging, 73
  - attenuated phase-shifting mask, 143
  - contrast, 83
  - ideal duty ratio, 143
  - ideal transmission, 145
  - imbalance beam intensities, 83
  - optimal illumination angle, 82
  - spatial period, 73
- UDOF, *see* usable depth of focus
- unmodified illumination, 71
- usable depth of focus, 64
- vector-scan mask writer, 95
- weak phase-shifting mask, *see* resolution enhancement technique, weak
- weak resolution enhancement technique, *see* resolution enhancement technique, weak
- x-ray lithography, 26
- Zernike polynomial, 128